



KEY FEATURES



10BB Half-cut Cell Technology

New circuit design, lower internal current, lower R_s loss
Ga doped wafer, attenuation <2% (1st year) / 0.45% (Linear)



Industry Leading High Yield

Bifacial PERC cell technology,
5%-25% more yield depends on different conditions



Excellent Anti-PID Performance

2 times of industry standard Anti-PID test



ELECTRICAL CHARACTERISTICS

	440	328	445	332	450	336	455	339	460	343
	34.35	32.1	34.53	32.2	34.70	32.4	34.87	32.6	35.04	32.7
	12.81	10.23	12.89	10.30	12.97	10.36	13.05	10.42	13.13	10.49
	40.99	38.6	41.16	38.7	41.33	38.9	41.50	39.1	41.67	39.2
	13.69	11.04	13.78	11.11	13.86	11.17	13.94	11.24	14.02	11.30
	20.30		20.50		20.70		21.00		21.20	

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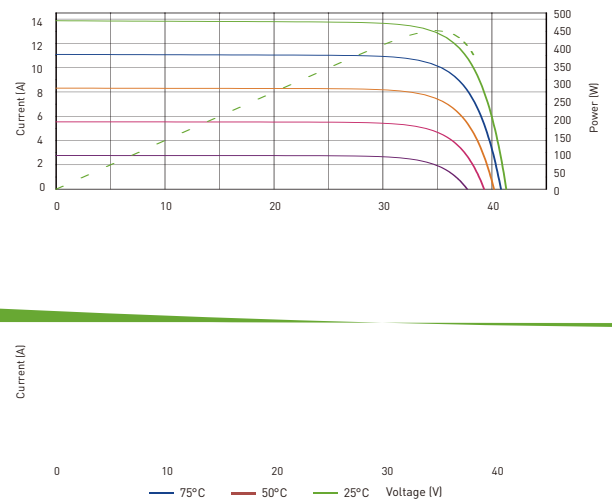
REAR SIDE POWER GAIN(REFERENCE TO 445W FRONT)

	5%	10%	15%	20%	25%
	467	490	512	534	556
	34.53	34.53	34.53	34.53	34.53
	13.53	14.18	14.82	15.47	16.11
	41.16	41.16	41.16	41.16	41.16
	14.47	15.16	15.85	16.54	17.23

MECHANICAL CHARACTERISTICS

	Monocrystalline Silicon (10Busbar)
	120pcs in series (6*20)
	1914*1134*30mm (75.35*44.65*1.18inches)
	26.8kg (59.1lbs)
	2.0mm AR Coating Semi-tempered Glass
	2.0mm Glazed Semi-tempered Glass
	Anodized Aluminium Alloy
	IP68, 3 Bypass Diodes
	4mm ² (IEC), 12AWG(UL)
	Length or Customized Length
	T01/LJQ-3-CSY/MC4/MC4-EV02

I-V CURVE



APPLICATION CONDITIONS

	1500V/DC
	-40°C~+85°C
	30A
	Class II
	Front side 5400Pa, Back side 2400Pa
	70%±5%

TEMPERATURE CHARACTERISTICS

	-0.35%/°C
	-0.26%/°C
	+0.048%/°C
	43±2°C

PACKING CONFIGURATION

	36	36(USA)
	864	684



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